



**GaN on SiC HEMT Pulsed Power Transistor**  
**250W Peak, 1200-1400 MHz, 300µs Pulse, 10% Duty**

**Production V1**  
**18 Aug 11**

## Features

- GaN depletion mode HEMT microwave transistor
- Internally matched
- Common source configuration
- Broadband Class AB operation
- RoHS Compliant
- +50V Typical Operation
- MTTF of 114 years (Channel Temperature < 200°C)

## Applications

- L-Band pulsed radar

## Product Description

The MAGX-001214-250L00 is a gold metalized matched Gallium Nitride (GaN) on Silicon Carbide RF power transistor optimized for pulsed L-Band radar applications. Using state of the art wafer fabrication processes, these high performance transistors provide high gain, efficiency, bandwidth, ruggedness over a wide bandwidth for today's demanding application needs. High breakdown voltages allow for reliable and stable operation in extreme mismatched load conditions unparalleled with older semiconductor technologies.



## Typical RF Performance at Pout = 250W Peak

Freq (MHz)	Pin (W)	Gain (dB)	Slope (dB)	Id (A)	Eff (%)	Avg-Eff (%)	RL (dB)	Droop (dB)
1200	4.4	17.6	-	8.0	62.2	-	-13.3	0.4
1250	4.0	18.0	-	8.2	60.4	-	-19.2	0.5
1300	4.1	17.8	-	8.7	57.1	-	-22.6	0.6
1350	4.4	17.5	-	9.1	54.6	-	-19.2	0.7
1400	4.4	17.6	0.5	9.0	55.0	57.9	-19.8	0.6

## Ordering Information

MAGX-001214-250L00 250W GaN Power Transistor  
 MAGX-001214-SB1PPR Evaluation Fixture

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**Absolute Maximum Ratings Table (1, 2, 3)**

Supply Voltage ( $V_{DD}$ )	+65V
Supply Voltage ( $V_{GS}$ )	-8 to -2V
Supply Current ( $I_{D_{MAX}}$ )	8.8 Apk
Input Power ( $P_{IN}$ )	+40 dBm
Absolute Max. Junction/Channel Temp	200 °C
MTTF ( $T_J < 200^\circ\text{C}$ )	114 years
Pulsed Power Dissipation at 85°C	192 Wpk
Thermal Resistance, ( $T_J = 70^\circ\text{C}$ ) $V_{DD} = 50\text{V}$ , $I_{DQ} = 250\text{mA}$ , $P_{out} = 250\text{W}$ 300µs Pulse / 10% Duty	0.60°C/W
Operating Temp	-40 to +95°C
Storage Temp	-65 to +150°C
Mounting Temperature	See solder reflow profile
ESD Min. - Machine Model (MM)	50V
ESD Min. - Human Body Model (HBM)	>250V
MSL Level	MSL1

(1) Operation of this device above any one of these parameters may cause permanent damage.

(2) Channel temperature directly affects a device's MTTF. Channel temperature should be kept as low as possible to maximize lifetime.

(3) For saturated performance it recommended that the sum of ( $3 \cdot V_{dd} + \text{abs}(V_{gg})$ ) < 175

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
<b>DC CHARACTERISTICS</b>						
Drain-Source Leakage Current	$V_{GS} = -8\text{V}$ , $V_{DS} = 175\text{V}$	$I_{DS}$	-	0.4	12	mA
Gate Threshold Voltage	$V_{DS} = 5\text{V}$ , $I_D = 30\text{mA}$	$V_{GS(th)}$	-5	-3.1	-2	V
Forward Transconductance	$V_{DS} = 5\text{V}$ , $I_D = 7.0\text{mA}$	$G_M$	5.0	7.7	-	S
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	Not applicable—Input internally matched	$C_{ISS}$	N/A	N/A	N/A	pF
Output Capacitance	$V_{DS} = 50\text{V}$ , $V_{GS} = -8\text{V}$ , $F = 1\text{MHz}$	$C_{OSS}$	-	22	-	pF
Feedback Capacitance	$V_{DS} = 50\text{V}$ , $V_{GS} = -8\text{V}$ , $F = 1\text{MHz}$	$C_{RSS}$	-	2.2	-	pF

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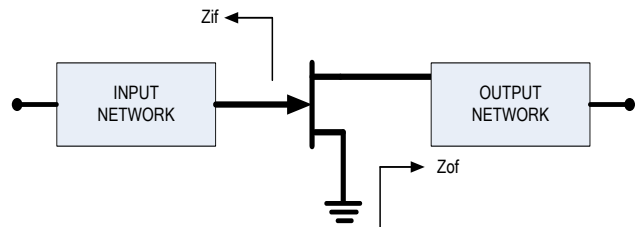
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**Electrical Specifications:  $T_C = 25 \pm 5^\circ\text{C}$  (Room Ambient )**

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
<b>RF FUNCTIONAL TESTS (<math>V_{DD} = 50\text{V}</math>, <math>I_{DQ} = 250\text{mA}</math>, 300us / 10% duty, 1200-1400MHz)</b>						
Input Power	$P_{out} = 250\text{W Peak (25W avg)}$	$P_{IN}$	-	4.2	5.6	Wpk
Power Gain	$P_{out} = 250\text{W Peak (25W avg)}$	$G_P$	16.5	17.7	-	dB
Drain Efficiency	$P_{out} = 250\text{W Peak (25W avg)}$	$\eta_D$	50	57.9	-	%
Load Mismatch Stability	$P_{out} = 250\text{W Peak (25W avg)}$	VSWR-S	5:1	-	-	-
Load Mismatch Tolerance	$P_{out} = 250\text{W Peak (25W avg)}$	VSWR-T	10:1	-	-	-

### Test Fixture Impedance

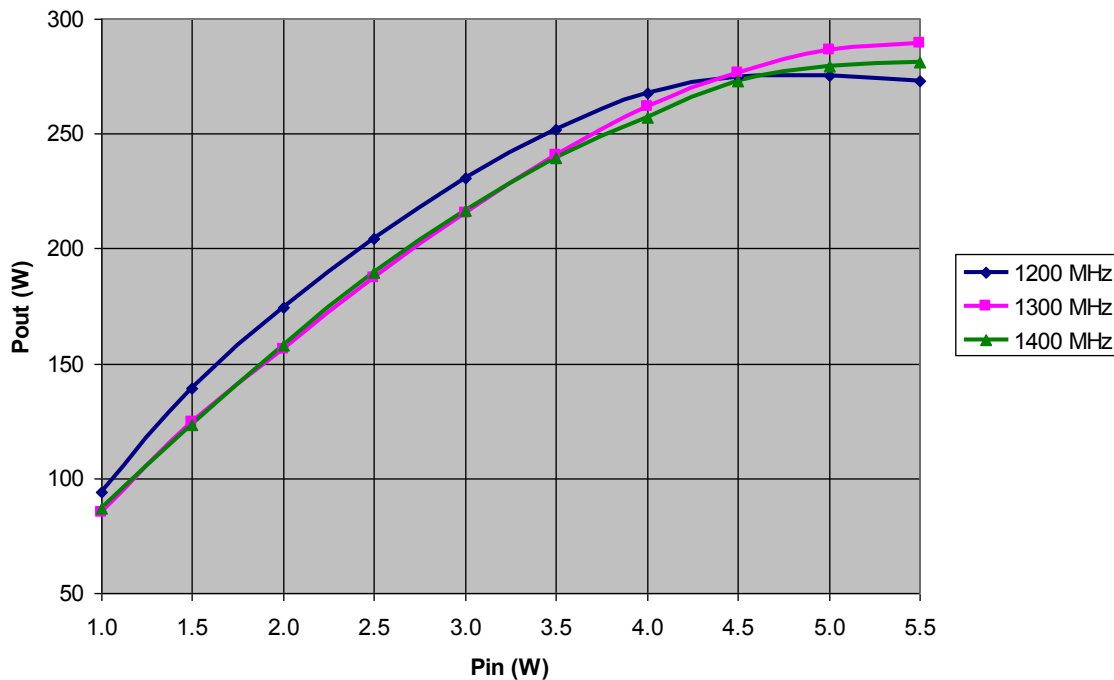
F (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
1200	$3.6 - j5.3$	$3.5 + j0.7$
1250	$3.3 - j4.9$	$3.7 + j0.2$
1300	$3.2 - j4.4$	$3.5 - j0.3$
1350	$3.2 - j4.0$	$3.2 - j0.6$
1400	$3.2 - j3.6$	$2.7 - j0.7$



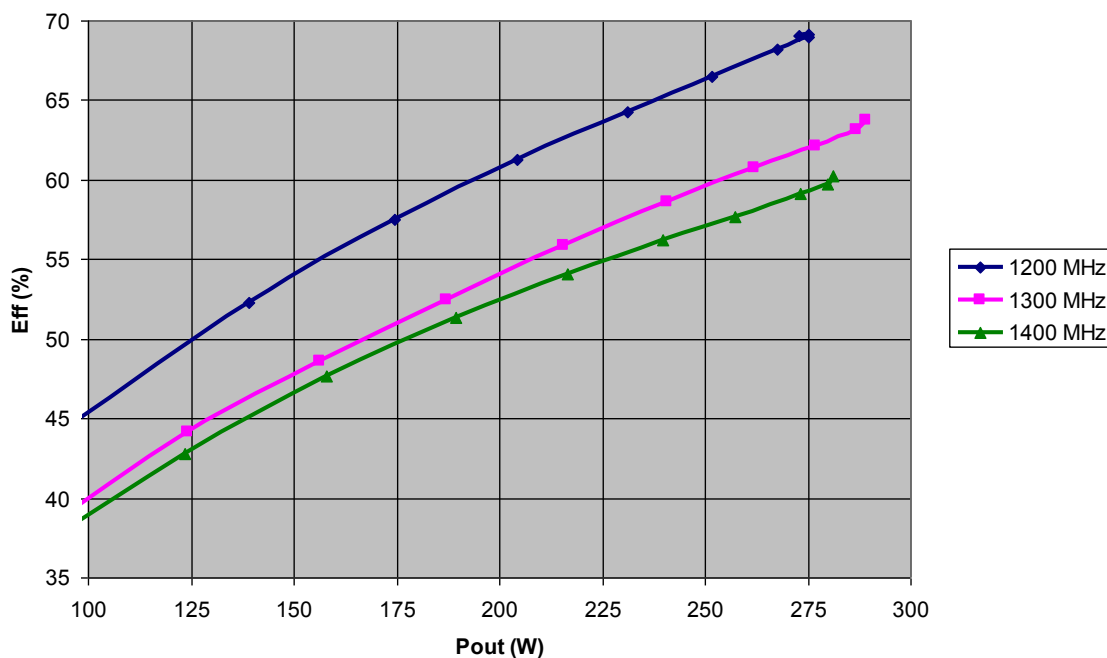
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### RF Power Transfer Curve (Output Power Vs. Input Power)



### RF Power Transfer Curve (Drain Efficiency Vs. Output Power)



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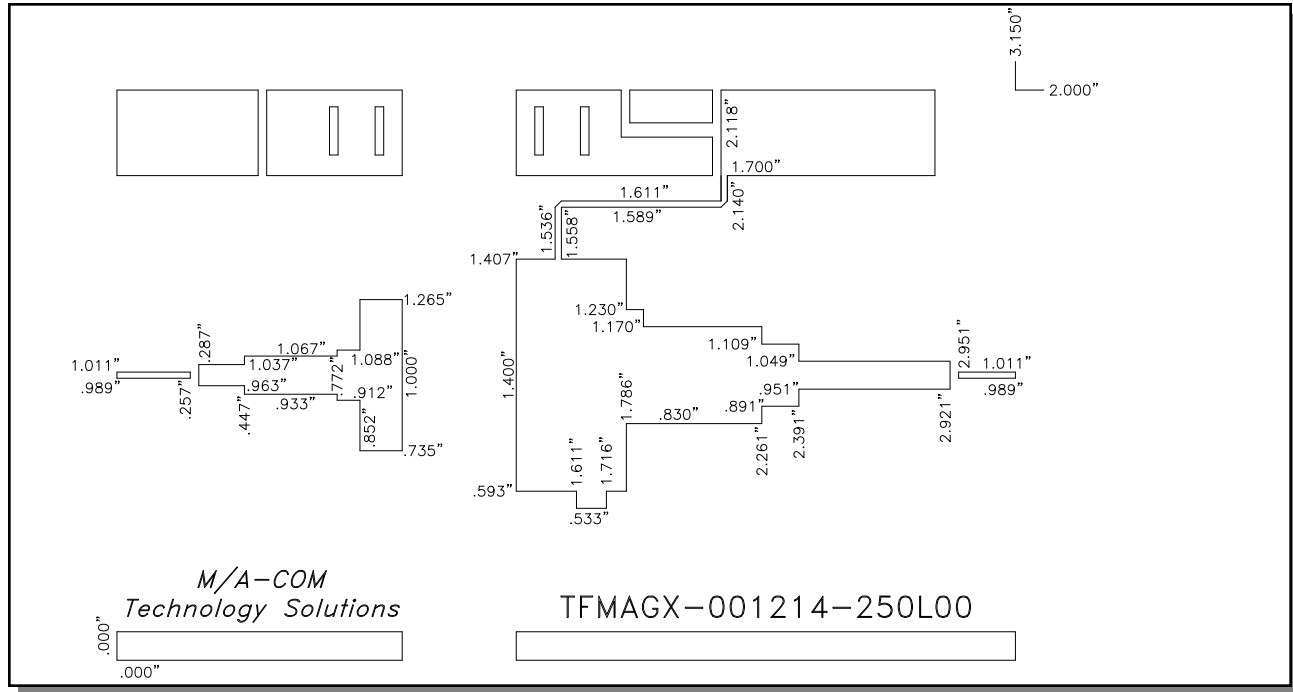
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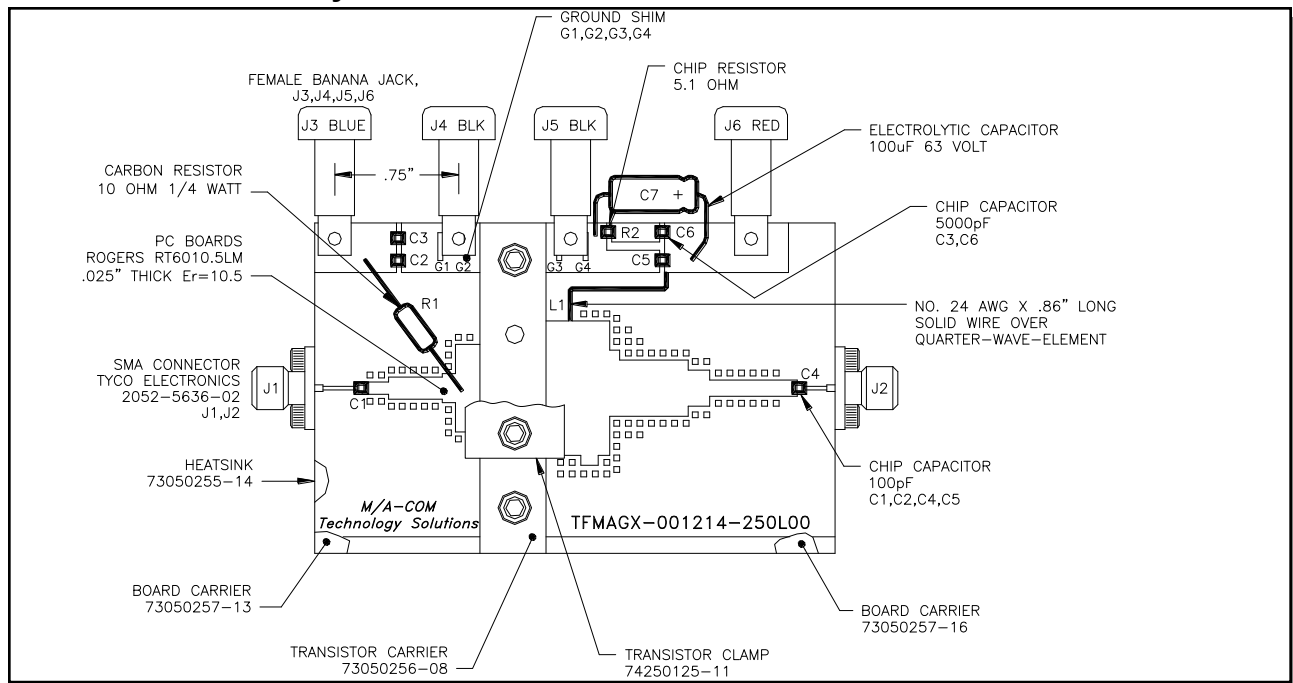
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## Test Fixture Circuit Dimensions



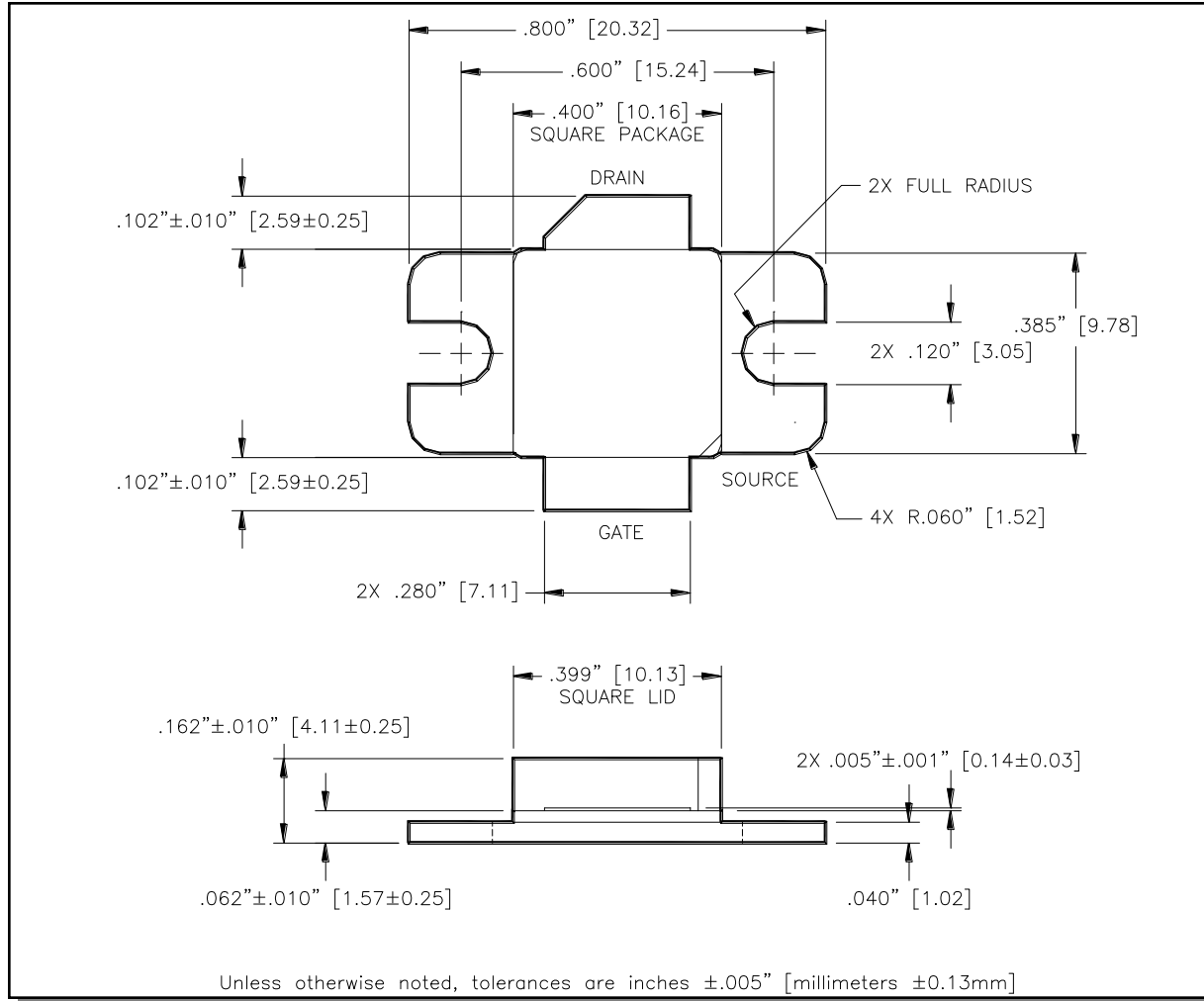
## Test Fixture Assembly



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## Outline Drawing



## CORRECT DEVICE SEQUENCING

### TURNING THE DEVICE ON

1. Set  $V_{GS}$  to the pinch-off ( $V_P$ ), typically -5V
2. Turn on  $V_{DS}$  to nominal voltage (50V)
3. Increase  $V_{GS}$  until the  $I_{DS}$  current is reached
4. Apply RF power to desired level

### TURNING THE DEVICE OFF

1. Turn the RF power off
2. Decrease  $V_{GS}$  down to  $V_P$
3. Decrease  $V_{DS}$  down to 0V
4. Turn off  $V_{GS}$

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